

Drafts Pending Active

- L1: (64281) MR or magnetoresist\$3
- L2: (89) 1 and equivalent near3 circuit same induc
- L3: (55) 2 and high near3 frequency

 Failed Saved Favorites Tracked (8)

[] USPAT US-PGP UB EPQ DERVENT IBM TDB

 Details Highlight cited items initially

Output operation: DB

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	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1	BRS	L1	64281	MR or magnetoresist\$3	USPAT; US-PGP; UB; EP	2004/01/29 14:27		
2	BRS	L2	89	1 and equivalent near3 circuit same induct\$4	USPAT; US-PGP; UB; EP	2004/01/29 14:29		
3	BRS	L3	55	2 and high near3 frequency	USPAT; US-PGP; UB; EP	2004/01/29 14:29		

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DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB Errors
Databases: DR Highlight citations only

Search Text:
 BRS Form SPC Form DDBS TDB IBM

Type	L #	Hits	Search Text	DBs	Time Stamp
1 BRS	L1	33	resistor same capacitor same inductor same magnetic near3 (head or transducer) and frequency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 12:48
2 BRS	L2	0	20020131216.URPN.	USPAT	2003/06/11 12:36
3 BRS	L3	3	tunnel\$3 same (MR or magnetoresist\$3) same induct\$4 same frequency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 12:49

Details HTML

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Find what:	Induct	Find Next					
Case:	<input type="radio"/> All	<input type="radio"/> Up	<input type="radio"/> Match word	<input type="radio"/> Whole	<input type="radio"/> Left	<input type="radio"/> Backward	<input type="radio"/> Cancel
Ctrl/Ctr:	<input type="radio"/> Sel/Ctr	<input type="radio"/> Down	<input type="radio"/> End	<input type="radio"/> Right	<input type="radio"/> Documents	<input type="checkbox"/> Match cases	

terminals (T3, T4) serve as output terminals. A current to change the magnetization direction of the magnetic tunnel resistance element (MR) is supplied through a current source (IP). With such a constitution, it is possible to provide an analog circuit, including a filter, a amplifier or the like, which can correct variations in value of elements caused by process variations in the manufacturing process.

Summary of Invention Paragraph - BSTX (3):

[0002] The present invention relates to a semiconductor memory device, and more particularly to a semiconductor device having a magnetic tunnel resistance element as a resistance element.

Summary of Invention Paragraph - BSTX (9):

[0008] In FIG. 40, the capacitor C is interposed between the terminals T1 and T3 and the resistor R is interposed between the wire connecting the terminals T2 and T4 and an electrode of the capacitor C on the side of the terminal T3. Further, the terminals T1 and T2 serve as input terminals and the terminals T3 and T4 serve as output terminals.

Summary of Invention Paragraph - BSTX (23):

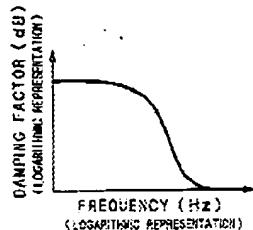
[0021] In FIG. 44, the resistor R and an inductor L are interposed, being connected in series, between the terminals T1 and T3 and the capacitor C is interposed between the wire connecting the terminals T2 and T4 and an end portion of the inductor L on the side of the terminal T3.

Summary of Invention Paragraph - BSTX (30):

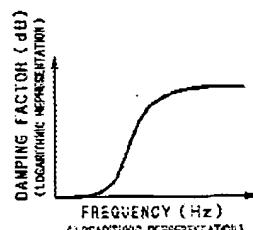
[0028] The LPF of FIG. 44 is represented by using the impedances Z1, Z2 and Z3 as shown in FIG. 46, and it is possible to form an LPF and an HPF by changing the combinations of passive elements (resistor, capacitor, inductor) which are assigned to these impedances.

Parent Application Publication Oct. 23, 2003 Sheet 23 of 28 US 2003/0198096 A1

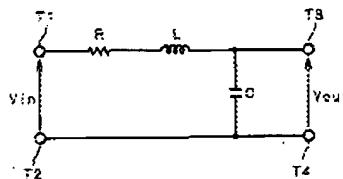
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F I G . 43
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F I G . 44
< BACKGROUND ART >



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INVENTOR-INFORMATION:

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GRAPHITIC NANOFIBERS IN
ELECTROCHEMICAL CAPACITORS

AMERICAN U.S. APPENDIX INDEX

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(60) Continuation of application No. 09/410, Oct. 1, 1999, now Pat. No. 6,414,536; division of application No. 08/856,657, 15, 1997, now Pat. No. 6,031,711.
(60) Provisional application No. 60/017,609, 15, 1996.

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(52) U.S. Cl.

(57) ABSTRACT

Graphitic nanofibers, which include tubular fulminy called "buckytubes"), nanotubes and are functionalized by chemical substitution, electrodes in electrochemical capacitors. The nanofiber based electrode increases the performance of electrochemical capacitors.

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